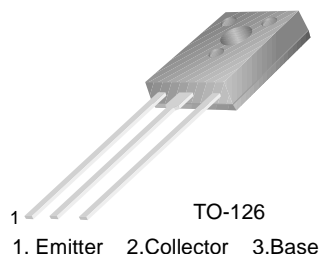


# KSP44M

KSP44M

## High Voltage Transistor

- Collector-Emitter Voltage :  $V_{CE0} = 400V$
- Collector Dissipation :  $P_C$  (Max.) = 1.2W



## NPN Epitaxial Silicon Transistor

### Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	500	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current	300	mA
$P_C$	Collector Dissipation ( $T_a = 25^\circ C$ )	1.2	W
$P_C$	Collector Dissipation ( $T_C = 25^\circ C$ )	10	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature	- 55 ~ 150	$^\circ C$

### Electrical Characteristics $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu A, I_E = 0$	500		V
$BV_{CEO}$	*Collector-Emitter Breakdown Voltage	$I_C = 1mA, I_B = 0$	400		V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100\mu A, I_C = 0$	6		V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 400V, I_E = 0$		0.1	$\mu A$
$I_{CES}$	Collector Cut-off Current	$V_{CE} = 400V, I_B = 0$		0.5	$\mu A$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 4V, I_C = 0$		0.1	$\mu A$
$h_{FE}$	*DC Current Gain	$V_{CE} = 10V, I_C = 1mA$ $V_{CE} = 10V, I_C = 10mA$ $V_{CE} = 10V, I_C = 50mA$ $V_{CE} = 10V, I_C = 100mA$	40 50 45 40	200	
$V_{CE(sat)}$	*Collector-Emitter Saturation Voltage	$I_C = 1mA, I_B = 0.1mA$ $I_C = 10mA, I_B = 1mA$ $I_C = 50mA, I_B = 5mA$		0.4 0.5 0.75	V V V
$V_{BE(sat)}$	*Base-Emitter Saturation Voltage	$I_C = 10mA, I_B = 1mA$		0.75	V
$C_{ob}$	Output Capacitance	$V_{CB} = 20V, I_E = 0$ $f = 1MHz$		7	pF

\* Pulse Test:  $PW \leq 300\mu s$ , Duty Cycle  $\leq 2\%$

# Typical Characteristics

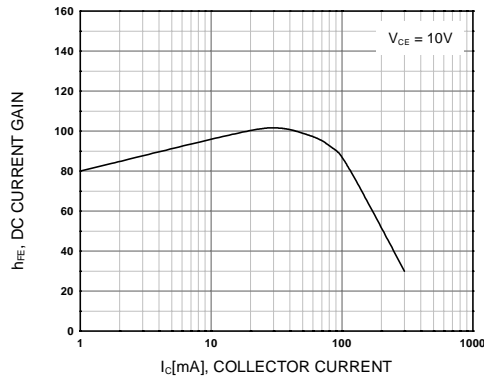


Figure 1. DC current Gain

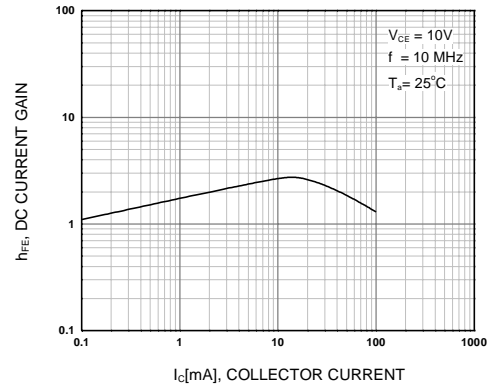


Figure 2. High Frequency Current Gain

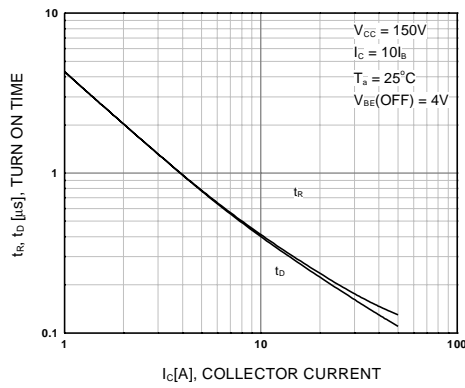


Figure 3. Turn On Switching Times

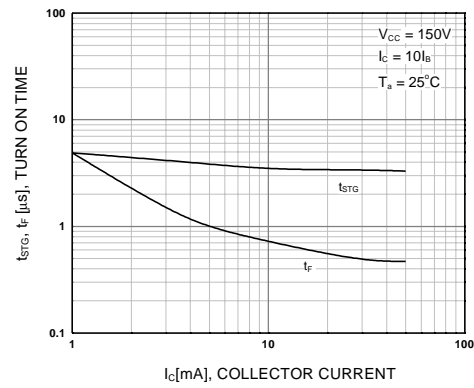


Figure 4. Turn Off Switching Times

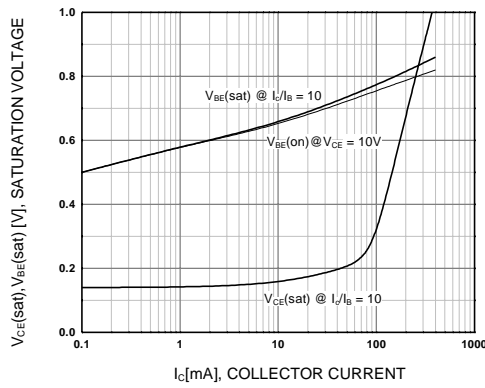


Figure 5. On Voltage

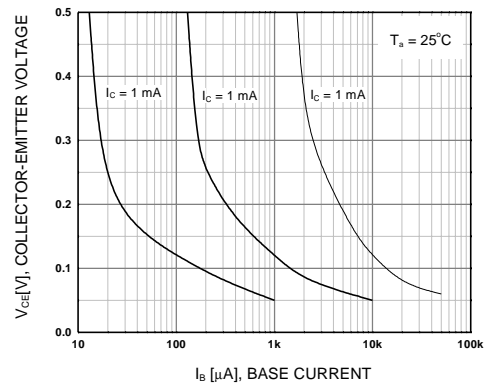


Figure 6. Collector Saturation Region

# Typical Characteristics (Continued)

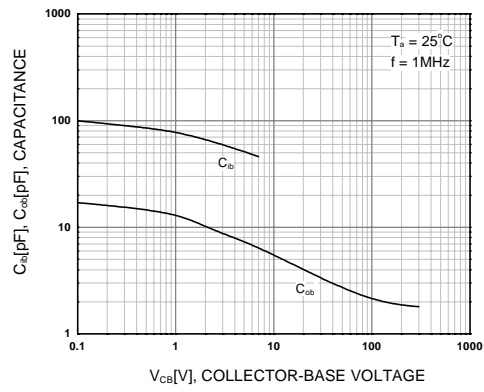


Figure 7. Capacitance

Technical drawing of the 2.28TYP connector showing three views: top, side, and front.

**Top View Dimensions:**

- Overall width:  $8.00 \pm 0.30$
- Overall height:  $14.20 \text{ MAX}$
- Top edge thickness:  $3.90 \pm 0.10$
- Central circular feature diameter:  $\phi 3.20 \pm 0.10$
- Bottom edge thickness:  $0.75 \pm 0.10$
- Internal width (left):  $1.60 \pm 0.10$
- Internal width (right):  $0.75 \pm 0.10$
- Bottom edge thickness (right):  $0.75 \pm 0.10$

**Side View Dimensions:**

- Overall height:  $16.10 \pm 0.20$
- Top edge thickness:  $3.25 \pm 0.20$
- Internal width (left):  $(1.00)$
- Internal width (right):  $(0.50)$
- Bottom edge thickness:  $1.75 \pm 0.20$
- Bottom edge thickness (right):  $0.50^{+0.10}_{-0.05}$

**Front View Dimensions:**

- Overall width:  $2.28 \text{ TYP}$  [ $2.28 \pm 0.20$ ]
- Overall height:  $13.06 \pm 0.30$
- Bottom edge thickness:  $0.75 \pm 0.10$
- Internal width (left):  $1.60 \pm 0.10$
- Internal width (right):  $0.75 \pm 0.10$
- Bottom edge thickness (right):  $0.75 \pm 0.10$

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